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[Vishay/Siliconix](#)  
[SI4804CDY-T1-GE3](#)

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**New Product**



**Si4804CDY**  
Vishay Siliconix

**Dual N-Channel 30-V (D-S) MOSFET**

| PRODUCT SUMMARY     |                                  |                                 |                       |
|---------------------|----------------------------------|---------------------------------|-----------------------|
| V <sub>DS</sub> (V) | R <sub>DS(on)</sub> (Ω)          | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |
| 30                  | 0.022 at V <sub>GS</sub> = 10 V  | 8                               | 7                     |
|                     | 0.027 at V <sub>GS</sub> = 4.5 V | 7.9                             |                       |

**FEATURES**

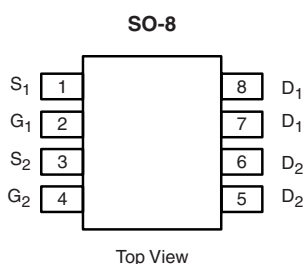
- Halogen-free
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested



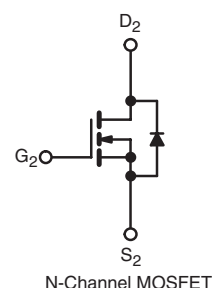
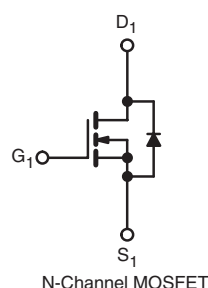
**RoHS**  
COMPLIANT

**APPLICATIONS**

- DC/DC
- Notebook System Power



**Ordering Information:** Si4804CDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



| ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted |                        |                                   |                      |      |
|-------------------------------------------------------------------------|------------------------|-----------------------------------|----------------------|------|
| Parameter                                                               |                        | Symbol                            | Limit                | Unit |
| Drain-Source Voltage                                                    |                        | V <sub>DS</sub>                   | 30                   | V    |
| Gate-Source Voltage                                                     |                        | V <sub>GS</sub>                   | ± 20                 |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C)                      | T <sub>C</sub> = 25 °C | I <sub>D</sub>                    | 8.0                  | A    |
|                                                                         | T <sub>C</sub> = 70 °C |                                   | 7.1                  |      |
|                                                                         | T <sub>A</sub> = 25 °C |                                   | 7.1 <sup>b, c</sup>  |      |
|                                                                         | T <sub>A</sub> = 70 °C |                                   | 5.5 <sup>b, c</sup>  |      |
| Pulsed Drain Current (10 μs Pulse Width)                                |                        | I <sub>DM</sub>                   | 30                   |      |
| Source-Drain Current Diode Current                                      | T <sub>C</sub> = 25 °C | I <sub>S</sub>                    | 2.4                  |      |
|                                                                         | T <sub>A</sub> = 25 °C |                                   | 1.8 <sup>b, c</sup>  |      |
| Pulsed Source-Drain Current                                             |                        | I <sub>SM</sub>                   | 30                   |      |
| Single Pulse Avalanche Current                                          | L = 0.1 mH             | I <sub>AS</sub>                   | 10                   | mJ   |
| Single Pulse Avalanche Energy                                           |                        | E <sub>AS</sub>                   | 5                    |      |
| Maximum Power Dissipation                                               | T <sub>C</sub> = 25 °C | P <sub>D</sub>                    | 3.1                  | W    |
|                                                                         | T <sub>C</sub> = 70 °C |                                   | 2                    |      |
|                                                                         | T <sub>A</sub> = 25 °C |                                   | 2 <sup>b, c</sup>    |      |
|                                                                         | T <sub>A</sub> = 70 °C |                                   | 1.28 <sup>b, c</sup> |      |
| Operating Junction and Storage Temperature Range                        |                        | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150          | °C   |

| THERMAL RESISTANCE RATINGS                  |              |                   |         |         |      |
|---------------------------------------------|--------------|-------------------|---------|---------|------|
| Parameter                                   |              | Symbol            | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient <sup>b, d</sup> | t ≤ 10 s     | R <sub>thJA</sub> | 49      | 62.5    | °C/W |
| Maximum Junction-to-Foot (Drain)            | Steady State | R <sub>thJF</sub> | 32      | 40      |      |

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 120 °C/W.

**New Product**

# Si4804CDY

Vishay Siliconix



| SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted |                                      |                                                                                                                                   |      |       |       |       |
|---------------------------------------------------------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|------|-------|-------|-------|
| Parameter                                                     | Symbol                               | Test Conditions                                                                                                                   | Min. | Typ.  | Max.  | Unit  |
| Static                                                        |                                      |                                                                                                                                   |      |       |       |       |
| Drain-Source Breakdown Voltage                                | V <sub>DS</sub>                      | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                    | 30   |       |       | V     |
| V <sub>DS</sub> Temperature Coefficient                       | ΔV <sub>DS</sub> /T <sub>J</sub>     | I <sub>D</sub> = 250 μA                                                                                                           |      | 31    |       | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient                   | ΔV <sub>GS(th)</sub> /T <sub>J</sub> |                                                                                                                                   |      | - 5.1 |       |       |
| Gate Threshold Voltage                                        | V <sub>GS(th)</sub>                  | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                       | 1.2  |       | 2.4   | V     |
| Gate Body Leakage                                             | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                                   |      |       | 100   | nA    |
| Zero Gate Voltage Drain Current                               | I <sub>DSS</sub>                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                                                                                     |      |       | 1     | μA    |
|                                                               |                                      | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                             |      |       | 10    |       |
| On-State Drain Current <sup>b</sup>                           | I <sub>D(on)</sub>                   | V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V                                                                                     | 20   |       |       | A     |
| Drain-Source On-State Resistance <sup>b</sup>                 | R <sub>DS(on)</sub>                  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.5 A                                                                                    |      | 0.018 | 0.022 | Ω     |
|                                                               |                                      | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6.5 A                                                                                   |      | 0.022 | 0.027 |       |
| Forward Transconductance <sup>b</sup>                         | g <sub>fs</sub>                      | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 7.5 A                                                                                    |      | 20    |       | S     |
| Dynamic <sup>a</sup>                                          |                                      |                                                                                                                                   |      |       |       |       |
| Input Capacitance                                             | C <sub>iss</sub>                     | N-Channel<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                             |      | 865   |       | pF    |
| Output Capacitance                                            | C <sub>oss</sub>                     |                                                                                                                                   |      | 131   |       |       |
| Reverse Transfer Capacitance                                  | C <sub>rss</sub>                     |                                                                                                                                   |      | 66    |       |       |
| Total Gate Charge                                             | Q <sub>g</sub>                       | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.5 A                                                            |      | 15.4  | 23    | nC    |
| Gate-Source Charge                                            | Q <sub>gs</sub>                      | N-Channel<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 7.5 A                                              |      | 7     | 10.5  |       |
| Gate-Drain Charge                                             | Q <sub>gd</sub>                      |                                                                                                                                   |      | 2.3   |       |       |
|                                                               |                                      |                                                                                                                                   |      | 2.2   |       |       |
| Gate Resistance                                               | R <sub>g</sub>                       | f = 1 MHz                                                                                                                         | 0.4  | 1.9   | 3.8   | Ω     |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | N-Channel<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  |      | 9     | 18    | ns    |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                                   |      | 12    | 24    |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                                   |      | 17    | 34    |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                                   |      | 9     | 18    |       |
| Turn-On Delay Time                                            | t <sub>d(on)</sub>                   | N-Channel<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |      | 17    | 34    |       |
| Rise Time                                                     | t <sub>r</sub>                       |                                                                                                                                   |      | 13    | 26    |       |
| Turn-Off Delay Time                                           | t <sub>d(off)</sub>                  |                                                                                                                                   |      | 19    | 35    |       |
| Fall Time                                                     | t <sub>f</sub>                       |                                                                                                                                   |      | 9     | 18    |       |
| Drain-Source Body Diode Characteristics                       |                                      |                                                                                                                                   |      |       |       |       |
| Continuous Source-Drain Diode Current                         | I <sub>S</sub>                       | T <sub>C</sub> = 25 °C                                                                                                            |      |       | 2.4   | A     |
| Pulse Diode Forward Current <sup>a</sup>                      | I <sub>SM</sub>                      |                                                                                                                                   |      |       | 30    |       |
| Body Diode Voltage                                            | V <sub>SD</sub>                      | I <sub>S</sub> = 1.8 A                                                                                                            |      | 0.77  | 1.1   | V     |
| Body Diode Reverse Recovery Time                              | t <sub>rr</sub>                      | N-Channel<br>I <sub>F</sub> = 5 A, dI/dt = 100 A/μs, T <sub>J</sub> = 25 °C                                                       |      | 16    | 32    | ns    |
| Body Diode Reverse Recovery Charge                            | Q <sub>rr</sub>                      |                                                                                                                                   |      | 8     | 16    | nC    |
| Reverse Recovery Fall Time                                    | t <sub>a</sub>                       |                                                                                                                                   |      | 10    |       | ns    |
| Reverse Recovery Rise Time                                    | t <sub>b</sub>                       |                                                                                                                                   |      | 6     |       |       |

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

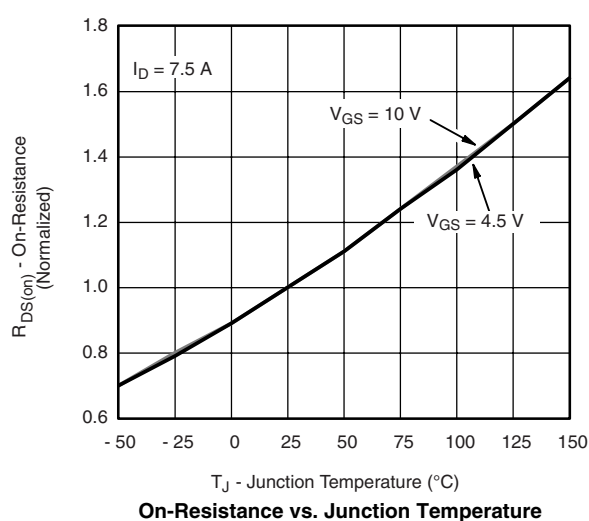
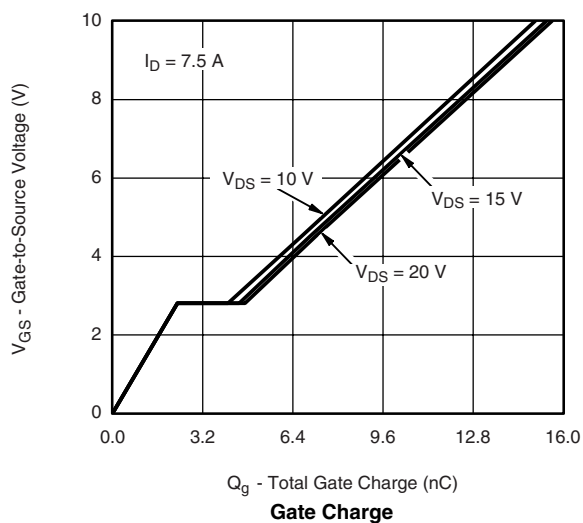
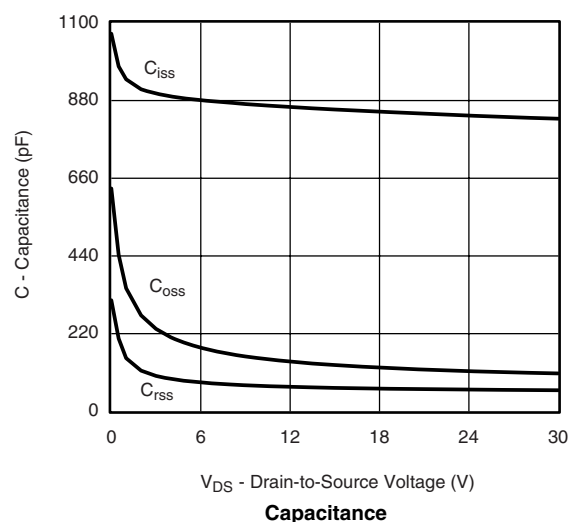
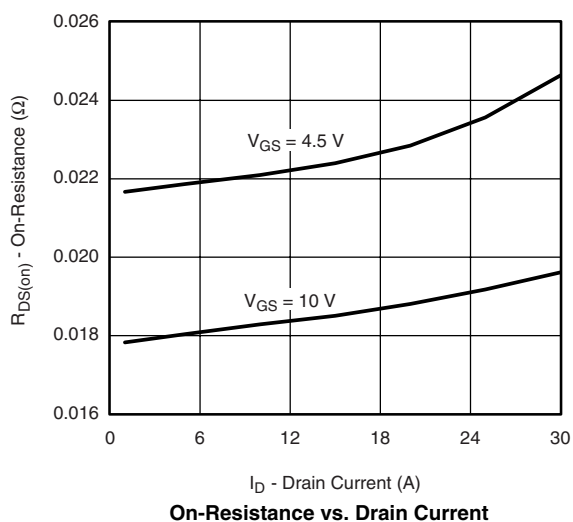
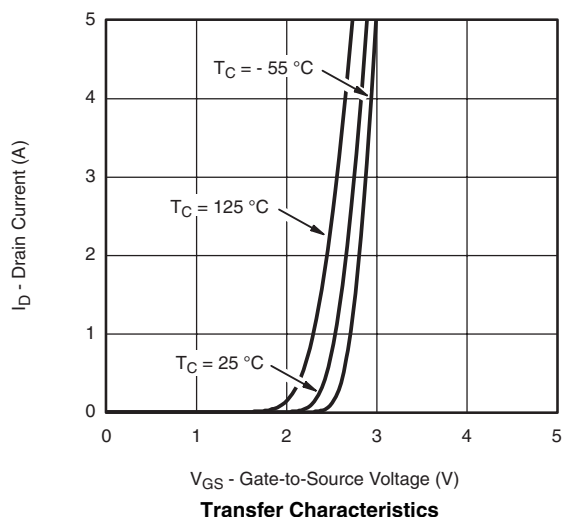
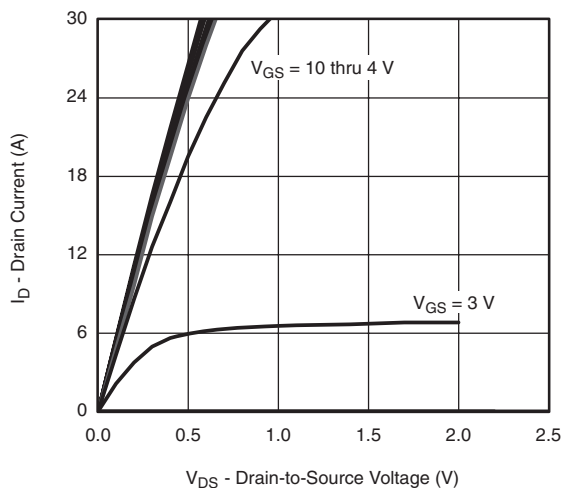
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**New Product**



**Si4804CDY**  
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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



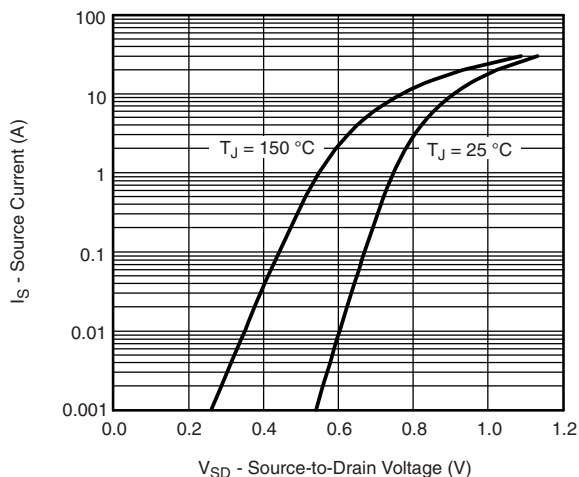
**New Product**

# Si4804CDY

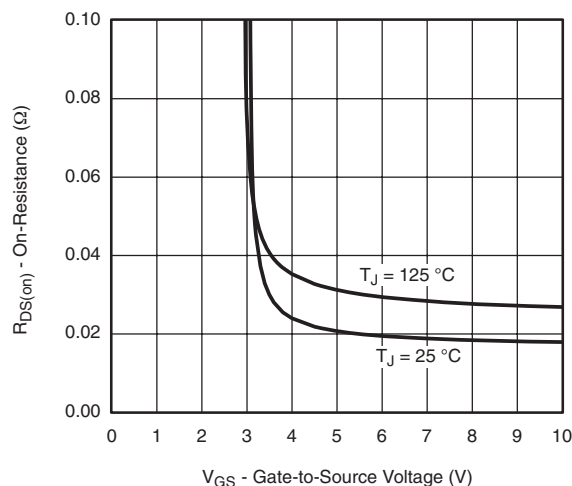
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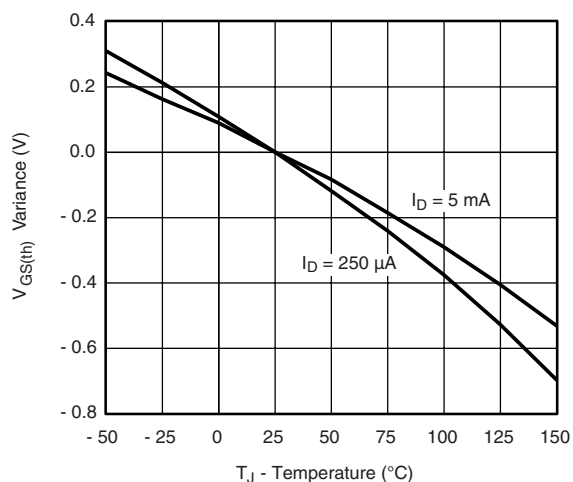
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



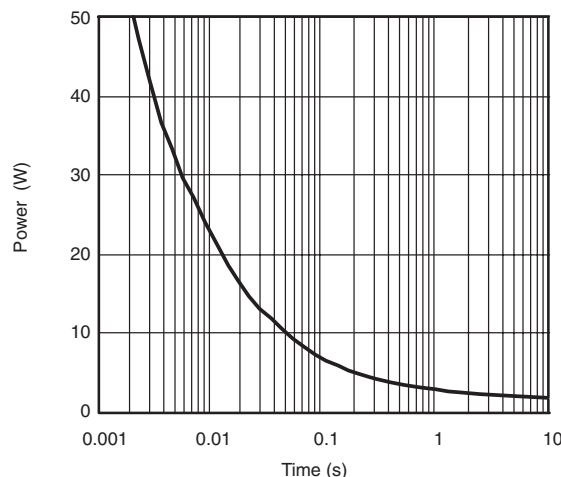
Source-Drain Diode Forward Voltage



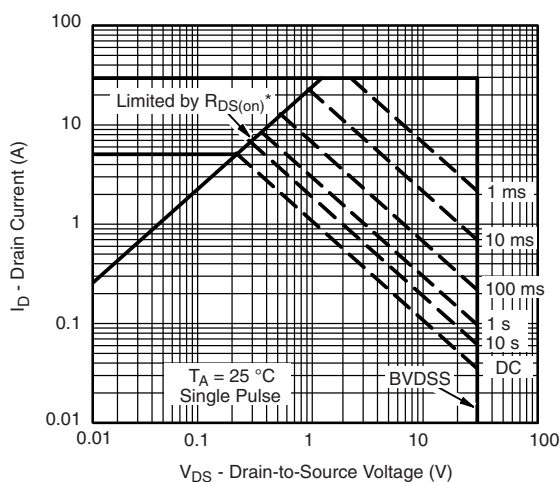
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

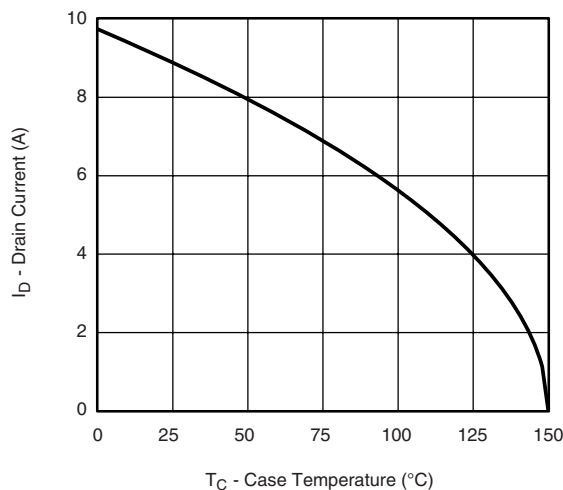
Safe Operating Area

**New Product**

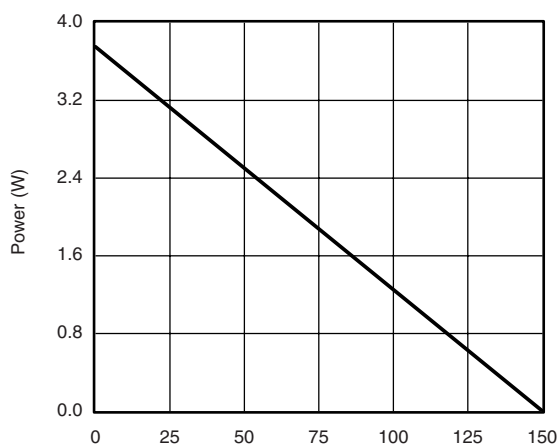


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**MOSFET TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

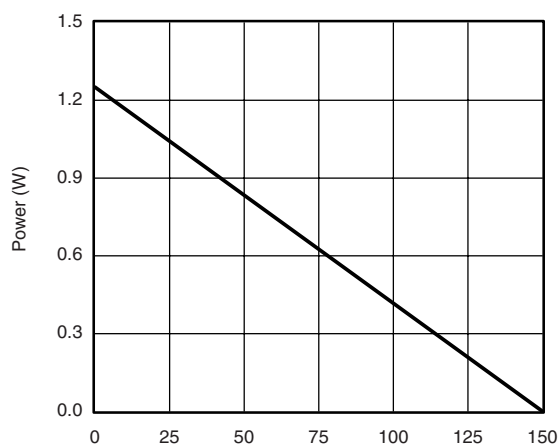


**Current Derating\***



$T_C$  - Case Temperature (°C)

**Power, Junction-to-Foot**



$T_A$  - Ambient Temperature (°C)

**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

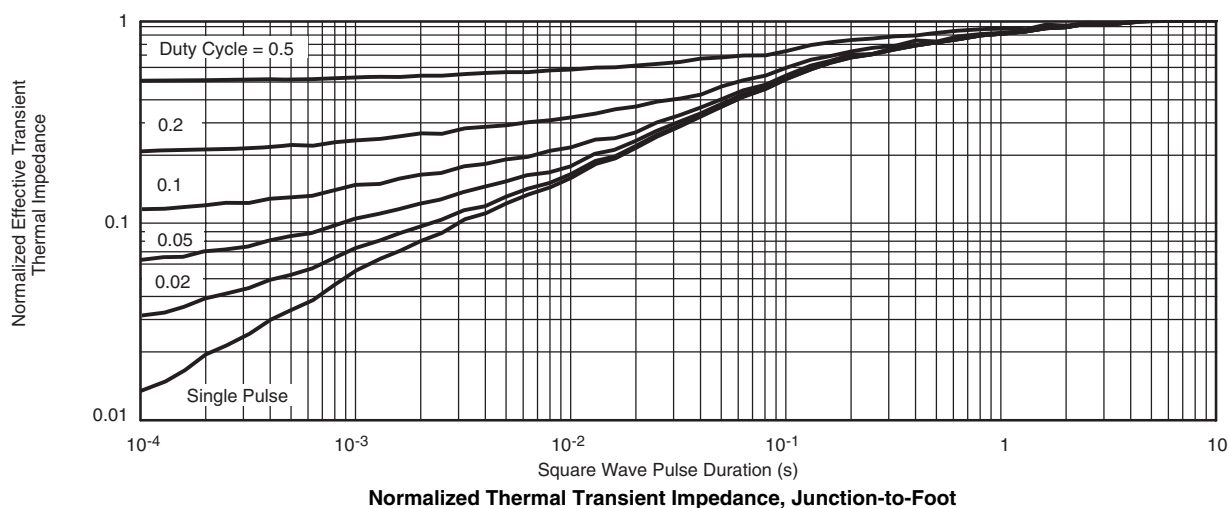
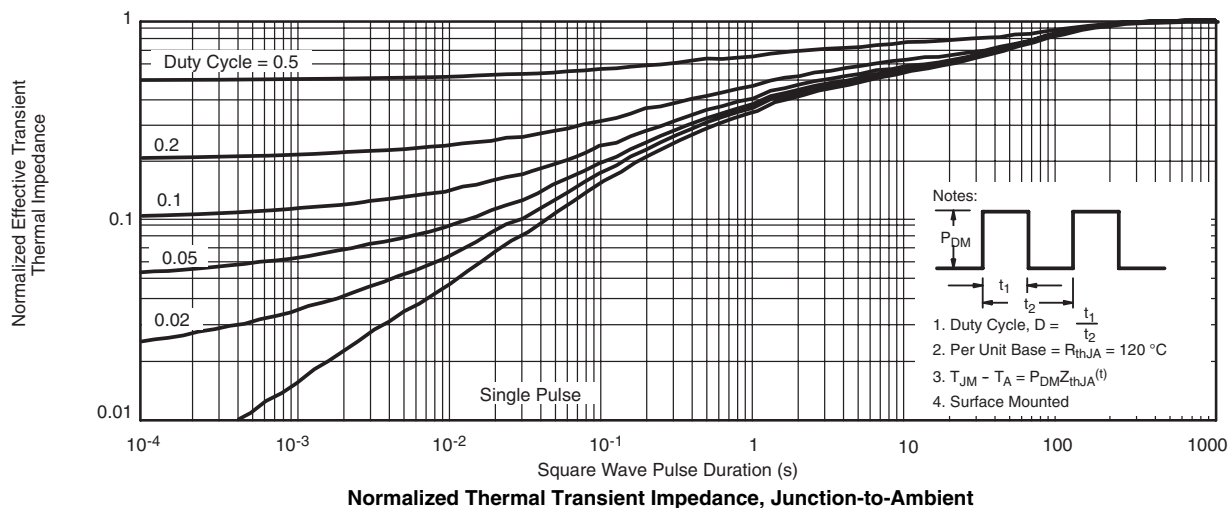
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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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